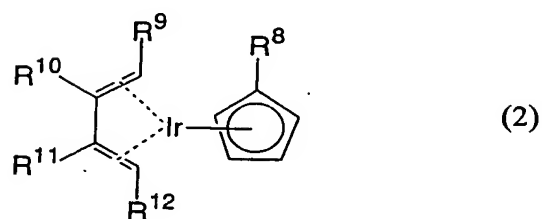
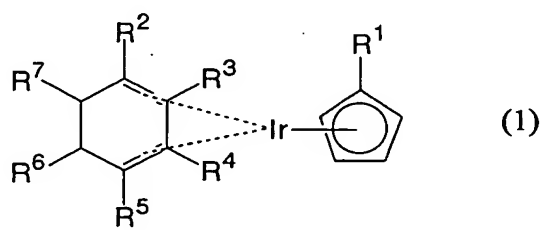


## ABSTRACT OF THE DISCLOSURE

An organometallic compound having a low melting point, excellent vaporization characteristic and low film formation temperature on a substrate, for forming an iridium-containing thin film by the CVD process is provided. The organometallic iridium compound is represented by the following general formula (1) or (2):



wherein R<sup>1</sup> represents hydrogen or a lower alkyl group; R<sup>2</sup> to R<sup>7</sup> each represents hydrogen, a halogen, or the like, provided that specific combinations of R<sup>1</sup> to R<sup>7</sup> are excluded; R<sup>8</sup> represents a lower alkyl group; R<sup>9</sup> to R<sup>12</sup> each represents hydrogen, a halogen, or the like, provided that specific combinations of R<sup>8</sup> to R<sup>12</sup> are excluded. Iridium-containing thin films are produced by using the compound as a precursor by CVD process.